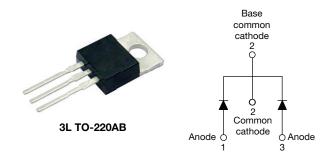
**Vishay Semiconductors** 

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# Ultrafast Rectifier, 10 A FRED Pt<sup>®</sup>



PRIMARY CHARACTERISTICS					
Package 3L TO-220AB					
I <sub>F(AV)</sub>	2 x 5 A				
V <sub>R</sub>	200 V				
V <sub>F</sub> at I <sub>F</sub>	0.87 V				
t <sub>rr</sub> typ.	See Recovery table				
T <sub>J</sub> max.	175 °C				
Circuit configuration	Common cathode				

## **FEATURES**

- Ultrafast recovery time
- · Low forward voltage drop
- 175 °C operating junction temperature
- Low leakage current
- Designed and gualified according to JEDEC<sup>®</sup>-JESD 47
- · Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

## **DESCRIPTION / APPLICATIONS**

VS-MUR.. series are the state of the art ultrafast recovery rectifiers specifically designed with optimized performance of forward voltage drop and ultrafast recovery time.

The planar structure and the platinum doped life time control, guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS							
PARAMETER		SYMBOL	TEST CONDITIONS	MAX.	UNITS		
Peak repetitive reverse voltage		V <sub>RRM</sub>		200	V		
Average restified forward surrant	per leg	1		5			
Average rectified forward current	total device	IF(AV)	Rated V <sub>R</sub> , T <sub>C</sub> = 149 °C	10			
Non-repetitive peak surge current per leg		I <sub>FSM</sub>		50	А		
Peak repetitive forward current per leg		I <sub>FM</sub>	Rated V <sub>R</sub> , square wave, 20 kHz $T_{C} = 149 \text{ °C}$	10			
Operating junction and storage temp	peratures	T <sub>J</sub> , T <sub>Stg</sub>		-65 to +175	°C		

<b>ELECTRICAL SPECIFICATIONS PER LEG</b> ( $T_J = 25 \text{ °C}$ unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Breakdown voltage, blocking voltage	V <sub>BR</sub> , V <sub>R</sub>	I <sub>R</sub> = 100 μA	200	-	-			
	V <sub>F</sub>	I <sub>F</sub> = 5 A, T <sub>J</sub> = 125 °C	-	0.87	0.99	V		
Forward voltage		I <sub>F</sub> = 10 A, T <sub>J</sub> = 125 °C	-	1.02	1.20			
		I <sub>F</sub> = 10 A	-	1.12	1.25			
		V <sub>R</sub> = V <sub>R</sub> rated	-	-	10			
Reverse leakage current	I <sub>R</sub>	$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	-	250	μA		
Junction capacitance	CT	V <sub>R</sub> = 200 V	-	8	-	pF		
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from package body	-	8.0	-	nH		

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<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS		
		$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t =$	50 A/µs, V <sub>R</sub> = 30 V	-	-	35			
Povorso rocovony timo	+	I <sub>F</sub> = 0.5 A, I <sub>R</sub> = 1.0 A, I <sub>REC</sub> = 0.25 A		-	-	25	ns		
Reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	24	-	115		
		T <sub>J</sub> = 125 °C		-	35	-			
Poak rocovony ourront	1	T <sub>J</sub> = 25 °C	I <sub>F</sub> = 5 A dI <sub>F</sub> /dt = 200 A/μs V <sub>B</sub> = 160 V	-	3.3	-	А		
Peak recovery current	I <sub>RRM</sub>	T <sub>J</sub> = 125 °C		-	5.0	-	A		
Reverse recovery charge	0	T <sub>J</sub> = 25 °C		-	33	-	20		
	Q <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	76	-	nC		

THERMAL MECHANICAL SPECIFICATIONS								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-65	-	175	°C		
Thermal resistance, junction to case per leg	R <sub>thJC</sub>		-	-	5			
Thermal resistance, junction to ambient per leg	R <sub>thJA</sub>		-	-	50	°C/W		
Thermal resistance, case to heatsink	R <sub>thCS</sub>	Mounting surface, flat, smooth, and greased	-	0.5	-			
Weight			-	2.0	-	g		
Weight			-	0.07	-	oz.		
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)		
Marking device		Case style 3L TO-220AB		MUR1	020CT			

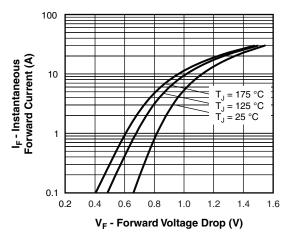
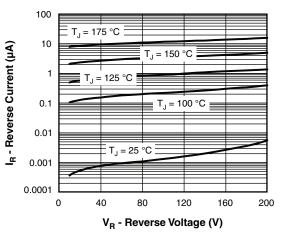
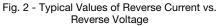


Fig. 1 - Typical Forward Voltage Drop Characteristics





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## VS-MUR1020CT-M3

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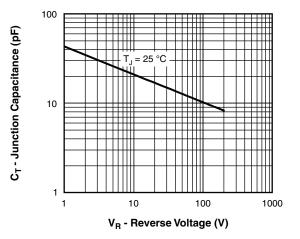


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

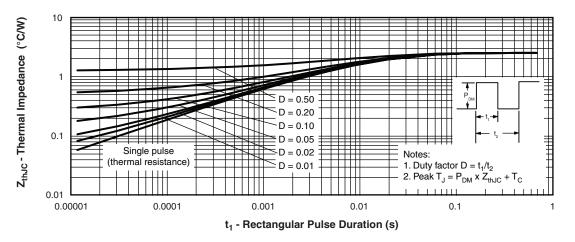
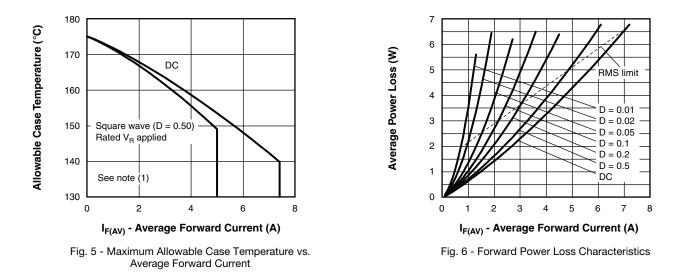


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics



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# **VS-MUR1020CT-M3**

## **Vishay Semiconductors**

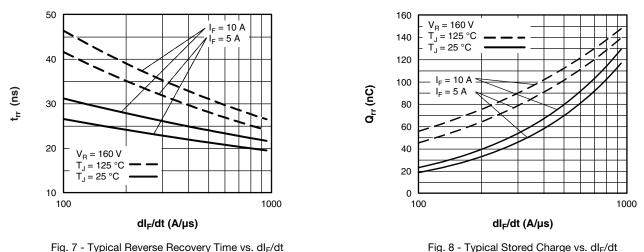


Fig. 8 - Typical Stored Charge vs. dl<sub>F</sub>/dt

#### Note

<sup>(1)</sup> Formula used:  $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$ ;  $\begin{array}{l} \mathsf{Pd} = \mathsf{Forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \times \mathsf{V}_{\mathsf{FM}} \ \mathsf{at} \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see} \ \mathsf{fig.} \ \mathsf{6}); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{Inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \times \mathsf{I}_{\mathsf{R}} \ (\mathsf{1} - \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ \mathsf{at} \ \mathsf{V}_{\mathsf{R1}} = \mathsf{Rated} \ \mathsf{V}_{\mathsf{R}} \end{array}$ 

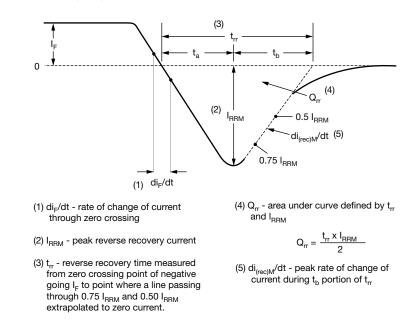


Fig. 9 - Reverse Recovery Waveform and Definitions

# VS-MUR1020CT-M3



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## **ORDERING INFORMATION TABLE**

Device code	VS-	MUR	10	20	СТ	-МЗ
	1	2	3	4	5	6
	1	- Vish	nay Sem	nicondu	ctors pr	oduct
	2	- Ultra	afast M	UR serie	es	
	3	- Cur	rent rati	ng (10 =	= 10 A)	
	4	- Volt	age rati	ing (20 =	= 200 V)	
	5	- CT	= cente	r tap (dı	ual) 3L 1	O-220A
	6	- Env	ironmer	ntal digit	t:	
		-M3	= halog	gen-free	, RoHS	-compli

ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-MUR1020CT-M3	50	1000	Antistatic plastic tube				

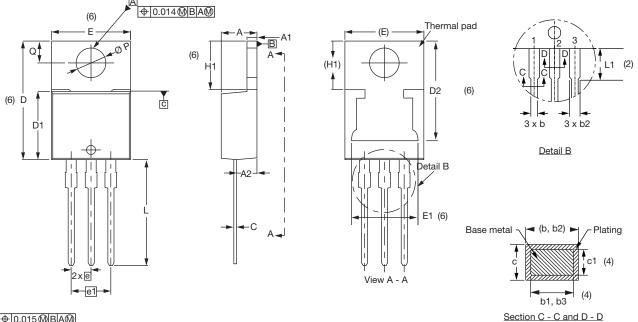
LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?96154
Part marking information	www.vishay.com/doc?95028



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## **3L TO-220AB**

### **DIMENSIONS** in millimeters and inches



⊕0.015@BA@





SYMBOL	MILLIN	IETERS	INC	NOTES	
STINDUL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.50	2.92	0.098	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.35	0.585	0.604	3
D1	8.38	9.02	0.330	0.355	

_		
Conforms to JEDEC <sup>®</sup>	outline	<b>TO-220AB</b>

SYMBOL	MILLIN	IETERS	INC	NOTES	
STINDOL	MIN.	MAX.	MIN.	MAX.	NOTES
D2	11.68	13.30	0.460	0.524	6, 7
Ш	10.11	10.51	0.398	0.414	3, 6
E1	6.86	8.89	0.270	0.350	6
е	2.41	2.67	0.095	0.105	
e1	4.88	5.28	0.192	0.208	
H1	6.09	6.48	0.240	0.255	6
L	13.52	14.02	0.532	0.552	
L1	3.32	3.82	0.131	0.150	2
ØР	3.54	3.91	0.139	0.154	
Q	2.60	3.00	0.102	0.118	

#### Notes

<sup>(2)</sup> Lead dimension and finish uncontrolled in L1

- <sup>(4)</sup> Dimension b1, b3, and c1 apply to base metal only
- (5) Controlling dimensions: inches
- <sup>(6)</sup> Thermal pad contour optional within dimensions E, H1, D2, and E1
- <sup>(7)</sup> Outline conforms to JEDEC<sup>®</sup> TO-220, except D2

Revision: 13-Jun-2019

 $<sup>^{(1)}\,</sup>$  Dimensioning and tolerancing as per ASME Y14.5M-1994

<sup>(3)</sup> Dimension D, D1, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body



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